

Wavelength	Type	Technology	Case
Infrared	Integrated filter	AlGaAs/GaAs	3 mm plastic lens

	<p><b>Description</b>                  Selective photodiode mounted in standard 3 mm package without standoff. Narrow bandwidth and high spectral sensitivity in the infrared range (810...950 nm).</p> <p>Note: Special packages with standoff available on request</p> <p><b>Applications</b>                  Alarm systems, light barriers, special sensors, analytics, optical communication</p>
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### Miscellaneous Parameters

$T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Active area		A	0.62	mm <sup>2</sup>
Temperature coefficient of $I_D$		$T_C(I_D)$	5	%/K
Operating temperature range		$T_{amb}$	-20 to +85	°C
Storage temperature range		$T_{stg}$	-30 to +100	°C
Soldering Temperature	$t \leq 3 \text{ s}$ , 3 mm from case	$T_{sld}$	260	°C
Acceptance angle at 50% $S_{\lambda}$		$\varphi$	60	deg.

### Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Breakdown voltage <sup>1)</sup>	$I_R = 10 \mu\text{A}$	$V_R$	5			V
Dark current	$V_R = 1 \text{ V}$	$I_D$		1.0	2.5	nA
Peak sensitivity wavelength	$V_R = 0 \text{ V}$	$\lambda_p$		890		nm
Responsivity at $\lambda_p$	$V_R = 0 \text{ V}$	$S_{\lambda}$	0.3	0.55		A/W
Sensitivity range at 10% <sup>1)</sup>	$V_R = 0 \text{ V}$	$\lambda_{min}, \lambda_{max}$	800		960	nm
Spectral bandwidth at 50%	$V_R = 0 \text{ V}$	$\Delta\lambda_{0.5}$		115		nm
Shunt resistance	$V_R = 10 \text{ mV}$	$R_{SH}$		115		GΩ
Noise equivalent power	$\lambda = 880 \text{ nm}$	NEP		$3.3 \times 10^{-14}$		W/ $\sqrt{\text{Hz}}$
Specific detectivity	$\lambda = 880 \text{ nm}$	$D^*$		$2.4 \times 10^{12}$		$\text{cm} \cdot \sqrt{\text{Hz}} \cdot \text{W}^{-1}$
Junction capacitance	$V_R = 0 \text{ V}$	$C_J$		120		pF
Switching time ( $R_L = 50 \Omega$ )	$V_R = 1 \text{ V}$	$t_r, t_f$		200		ns
Photo-current at $\lambda_p = 875 \text{ nm}$	$V_R = 0 \text{ V}$ $E_e = 1 \text{ mW/cm}^2$	$I_{Ph}$		14		$\mu\text{A}$

<sup>1)</sup>for information only

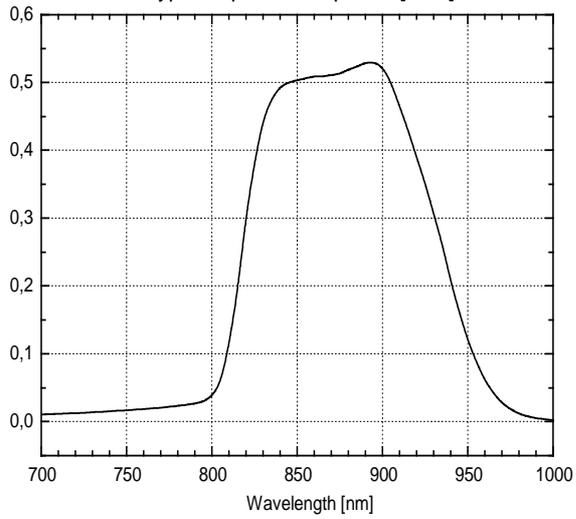
<sup>2)</sup> Halogen lamp source with appropriate filter

Note: All measurements carried out with *EPIGAP* equipment

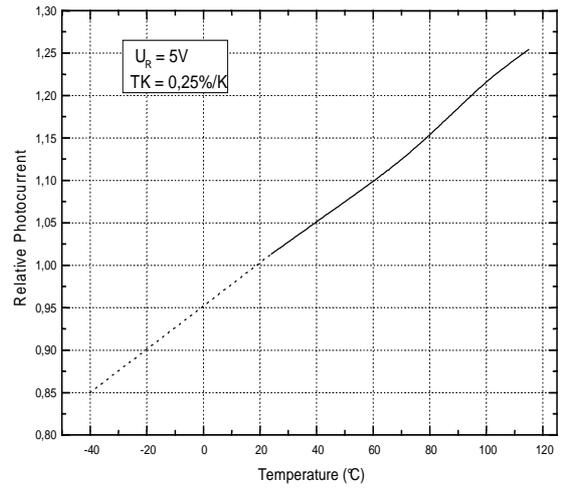
### Labeling

Type	Lot N°	$R_D$ (typ.) [GΩ]	Quantity
EPD-880-3-0.9			

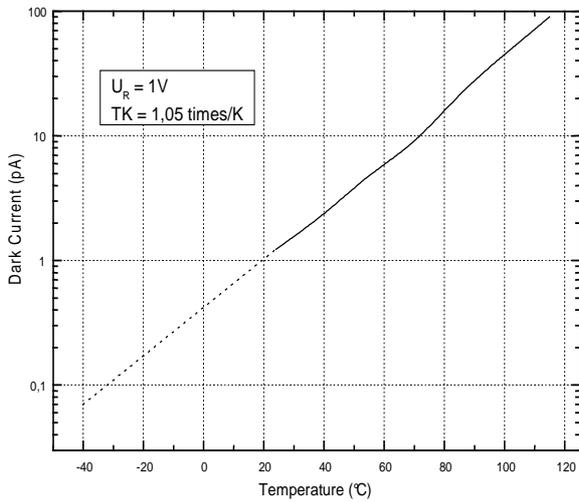
Typical spectral response [A/W]



Relative Photocurrent vs. Temperature



Dark Current vs. Temperature



Short-circuit current vs. irradiance (typical) <sup>2)</sup>

